

Abstract of the Disclosure

A method for fabricating a conducting layer pattern using a hard mask of which a upper surface is
5 flattened by the use of ArF exposure light source. The
method includes the steps of: forming a conducting layer
on a semiconductor substrate; forming a first hard mask
layer, a second hard mask layer and a third hard mask
layer on the conducting layer in order; forming a
10 photoresist pattern on the third hard mask layer using an
ArF exposure light source in order to form a predetermined
pattern; forming a first hard mask pattern by etching the
third hard mask layer using the photoresist pattern as an
etching mask; forming a second hard mask pattern by
15 etching the second hard mask layer using the first hard
mask pattern as an etching mask; removing the first hard
mask pattern; and etching the first hard mask layer and
the conducting layer using the second hard mask pattern as
an etching mask and forming a stacked hard mask pattern
20 having the conducting layer and the second and first hard
mask patterns, whereby a spire-shaped pattern is removed
from the stacked hard mask pattern.